

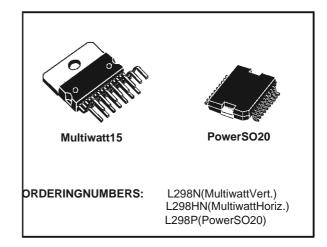
# **DUALFULL-BRIDGEDRIVER**

OPERATINGSUPPLYVOLTAGEUPTO46V

- TOTALDCCURRENTUPTO4A
- LOWSATURATIONVOLTAGE
- OVERTEMPERATUREPROTECTION
- LOGICAL"0"INPUTVOLTAGEUPTO1.5V
- (HIGHNOISEIMMUNITY)

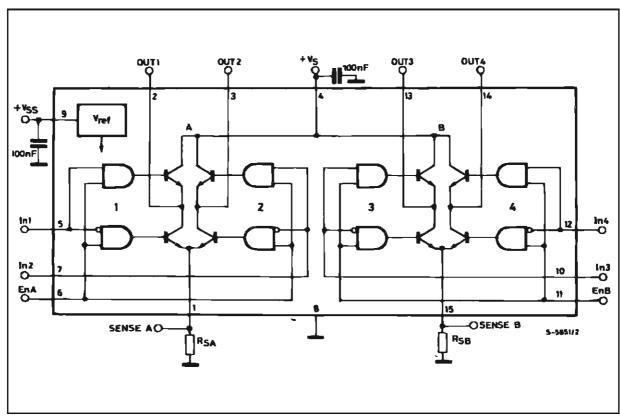
#### **DESCRIPTION**

TheL298isanintegratedmonolithiccircuitina15-leadMultiwattandPowerSO20packages.Itisa highvoltage,highcurrentdualfull-bridgedriverdesignedtoacceptstandardTTLlogiclevelsanddrive inductiveloadssuchasrelays,solenoids,DCand steppingmotors.Twoenableinputsareprovidedto enableordisablethedeviceindependentlyoftheinputsignals.Theemittersofthelowertransistorsof eachbridgeareconnectedtogetherandthecorrespondingexternalterminalcanbeusedforthecon-



nectionofanexternalsensingresistor. Anadditional supplyinputisprovided so that the logic works at a lower voltage.

#### **BLOCKDIAGRAM**

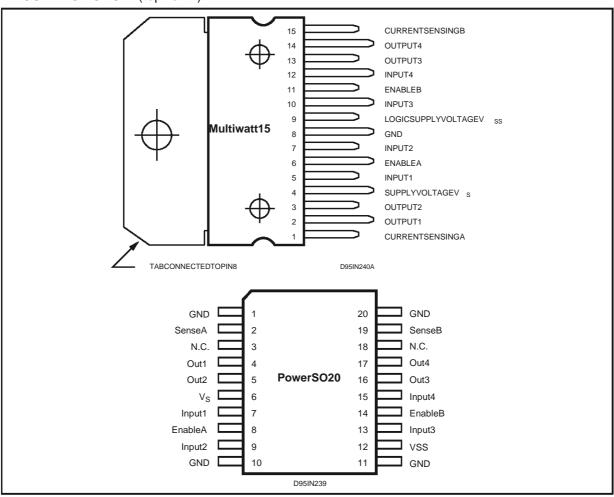


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#### **ABSOLUTEMAXIMUMRATINGS**

Symbol	Parameter	Value	Unit
Vs	PowerSupply	50	V
Vss	LogicSupplyVoltage	7	V
V <sub>I</sub> ,V <sub>en</sub>	InputandEnableVoltage	-0.3to7	V
lo	PeakOutputCurrent(eachChannel) -NonRepetitive(t=100 µs) -Repetitive(80%on-20%off;t on =10 ms) -DCOperation	3 2.5 2	A A A
V <sub>sens</sub>	SensingVoltage	-1to2.3	V
Ptot	TotalPowerDissipation(T case =75 °C)	25	W
Тор	JunctionOperatingTemperature	-25to130	°C
T <sub>stg</sub> ,T j	StorageandJunctionTemperature	-40to150	°C

### PINCONNECTIONS (topview )



### **THERMALDATA**

Symbol	Parameter		PowerSO20	Multiwatt15	Unit
R <sub>thj-case</sub>	ThermalResistanceJunction-case	Max.	_	3	°C/W
R <sub>thj-amb</sub>	ThermalResistanceJunction-ambient	Max.	13(*)	35	°C/W

(\*) Mountedonaluminumsubstrate

## PIN FUNCTIONS (refer to the block diagram)

MW.15	PowerSO	Name	Function
1;15	2;19	Sense A; Sense B	Between this pin and ground is connected the sense resistor to control the current of the load.
2;3	4;5	Out 1; Out 2	Outputs of the Bridge A; the current that flows through the load connected between these two pins is monitored at pin 1.
4	6	Vs	Supply Voltage for the Power Output Stages. A non-inductive 100nF capacitor must be connected between this pin and ground.
5;7	7;9	Input 1; Input 2	TTL Compatible Inputs of the Bridge A.
6;11	8;14	Enable A; Enable B	TTL Compatible Enable Input: the L state disables the bridge A (enable A) and/or the bridge B (enable B).
8	1,10,11,20	GND	Ground.
9	12	VSS	Supply Voltage for the Logic Blocks. A100nF capacitor must be connected between this pin and ground.
10; 12	13;15	Input 3; Input 4	TTL Compatible Inputs of the Bridge B.
13; 14	16;17	Out 3; Out 4	Outputs of the Bridge B. The current that flows through the load connected between these two pins is monitored at pin 15.
_	3;18	N.C.	Not Connected

# $\textbf{ELECTRICAL CHARACTERISTICS} \ (V_S = 42V; V_{SS} = 5V, T_j = 25^{\circ}C; unless \ otherwise \ specified)$

Symbol	Parameter	Test Conditi	ons	Min.	Тур.	Max.	Unit
Vs	Supply Voltage (pin 4)	Operative Condition		V <sub>IH</sub> +2.5		46	V
$V_{SS}$	Logic Supply Voltage (pin 9)			4.5	5	7	V
Is	Quiescent Supply Current (pin 4)	V <sub>en</sub> = H; I <sub>L</sub> = 0	$V_i = L$ $V_i = H$		13 50	22 70	mA mA
		V <sub>en</sub> = L	$V_i = X$			4	mA
I <sub>SS</sub>	Quiescent Current from V <sub>SS</sub> (pin 9)	V <sub>en</sub> = H; I <sub>L</sub> = 0	$V_i = L$ $V_i = H$		24 7	36 12	mA mA
		V <sub>en</sub> = L	$V_i = X$			6	mA
$V_{iL}$	Input Low Voltage (pins 5, 7, 10, 12)			-0.3		1.5	٧
V <sub>iH</sub>	Input High Voltage (pins 5, 7, 10, 12)			2.3		VSS	٧
l <sub>iL</sub>	Low Voltage Input Current (pins 5, 7, 10, 12)	$V_i = L$				-10	μΑ
I <sub>iH</sub>	High Voltage Input Current (pins 5, 7, 10, 12)	$Vi = H \le V_{SS} - 0.6V$			30	100	μА
V <sub>en</sub> = L	Enable Low Voltage (pins 6, 11)			-0.3		1.5	V
V <sub>en</sub> = H	Enable High Voltage (pins 6, 11)			2.3		V <sub>SS</sub>	V
I <sub>en</sub> = L	Low Voltage Enable Current (pins 6, 11)	V <sub>en</sub> = L				-10	μΑ
I <sub>en</sub> = H	High Voltage Enable Current (pins 6, 11)	$V_{en} = H \le V_{SS} - 0.6V$			30	100	μΑ
V <sub>CEsat(H)</sub>	Source Saturation Voltage	I <sub>L</sub> = 1A I <sub>L</sub> = 2A		0.95	1.35 2	1.7 2.7	V V
V <sub>CEsat(L)</sub>	Sink Saturation Voltage	I <sub>L</sub> = 1A (5) I <sub>L</sub> = 2A (5)		0.85	1.2 1.7	1.6 2.3	V
V <sub>CEsat</sub>	Total Drop	I <sub>L</sub> = 1A (5) I <sub>L</sub> = 2A (5)		1.80		3.2 4.9	V
V <sub>sens</sub>	Sensing Voltage (pins 1, 15)			-1 (1)		2	V



### **ELECTRICAL CHARACTERISTICS** (continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
T <sub>1</sub> (V <sub>i</sub> )	Source Current Turn-off Delay	0.5 V <sub>i</sub> to 0.9 I <sub>L</sub> (2); (4)		1.5		μs
T <sub>2</sub> (V <sub>i</sub> )	Source Current Fall Time	0.9 I <sub>L</sub> to 0.1 I <sub>L</sub> (2); (4)		0.2		μs
T <sub>3</sub> (V <sub>i</sub> )	Source Current Turn-on Delay	0.5 V <sub>i</sub> to 0.1 I <sub>L</sub> (2); (4)		2		μs
T <sub>4</sub> (V <sub>i</sub> )	Source Current Rise Time	0.1 I <sub>L</sub> to 0.9 I <sub>L</sub> (2); (4)		0.7		μs
T <sub>5</sub> (V <sub>i</sub> )	Sink Current Turn-off Delay	0.5 V <sub>i</sub> to 0.9 I <sub>L</sub> (3); (4)		0.7		μs
T <sub>6</sub> (V <sub>i</sub> )	Sink Current Fall Time	0.9 I <sub>L</sub> to 0.1 I <sub>L</sub> (3); (4)		0.25		μs
T <sub>7</sub> (V <sub>i</sub> )	Sink Current Turn-on Delay	0.5 V <sub>i</sub> to 0.9 I <sub>L</sub> (3); (4)		1.6		μs
T <sub>8</sub> (V <sub>i</sub> )	Sink Current Rise Time	0.1 I <sub>L</sub> to 0.9 I <sub>L</sub> (3); (4)		0.2		μs
fc (V <sub>i</sub> )	Commutation Frequency	I <sub>L</sub> = 2A		25	40	KHz
T <sub>1</sub> (V <sub>en</sub> )	Source Current Turn-off Delay	0.5 V <sub>en</sub> to 0.9 I <sub>L</sub> (2); (4)		3		μs
T <sub>2</sub> (V <sub>en</sub> )	Source Current Fall Time	0.9 I <sub>L</sub> to 0.1 I <sub>L</sub> (2); (4)		1		μs
T <sub>3</sub> (V <sub>en</sub> )	Source Current Turn-on Delay	0.5 V <sub>en</sub> to 0.1 I <sub>L</sub> (2); (4)		0.3		μs
T <sub>4</sub> (V <sub>en</sub> )	Source Current Rise Time	0.1 I <sub>L</sub> to 0.9 I <sub>L</sub> (2); (4)		0.4		μs
T <sub>5</sub> (V <sub>en</sub> )	Sink Current Turn-off Delay	0.5 V <sub>en</sub> to 0.9 I <sub>L</sub> (3); (4)		2.2		μs
T <sub>6</sub> (V <sub>en</sub> )	Sink Current Fall Time	0.9 I <sub>L</sub> to 0.1 I <sub>L</sub> (3); (4)		0.35		μs
T <sub>7</sub> (V <sub>en</sub> )	Sink Current Turn-on Delay	0.5 V <sub>en</sub> to 0.9 I <sub>L</sub> (3); (4)		0.25		μs
T <sub>8</sub> (V <sub>en</sub> )	Sink Current Rise Time	0.1 I <sub>L</sub> to 0.9 I <sub>L</sub> (3); (4)		0.1		μs

<sup>1) 1)</sup>Sensing voltage can be –1 V for t  $\leq$  50  $\mu sec;$  in steady state V  $_{sens}$  min  $\geq$  –0.5 V. 2) See fig. 2. 3) See fig. 4.

Figure 1: Typical Saturation Voltage vs. Output Current.

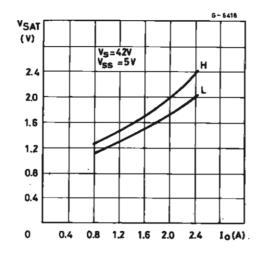
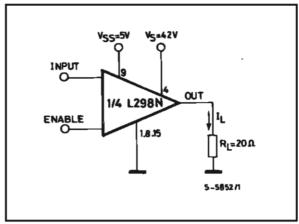


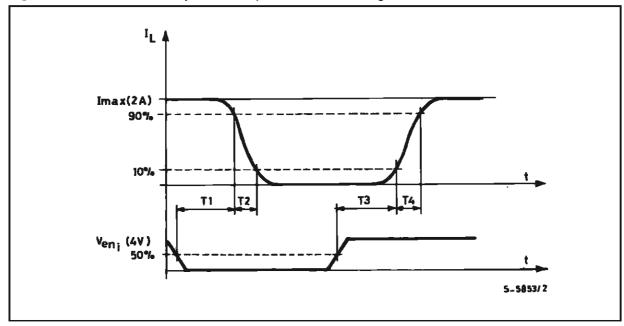
Figure 2: Switching Times Test Circuits.



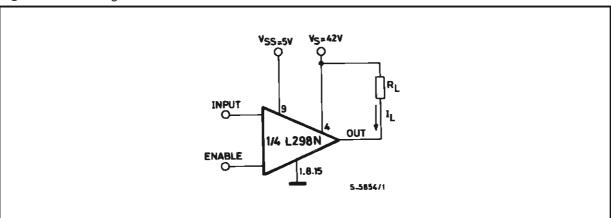
Note: For INPUT Switching, set EN = H
For ENABLESwitching, set IN = H

<sup>4)</sup> The load must be a pure resistor.

Figure3: SourceCurrentDelayTimesvs.InputorEnableSwitching.



**Figure4:** SwitchingTimesTestCircuits.



**Note:** ForINPUTSwitching,setEN=H ForENABLESwitching,setIN=L

 $\textbf{Figure 5:} \hspace{0.2in} \textbf{SinkCurrentDelayTimesvs.Input0VEnableSwitching}.$ 

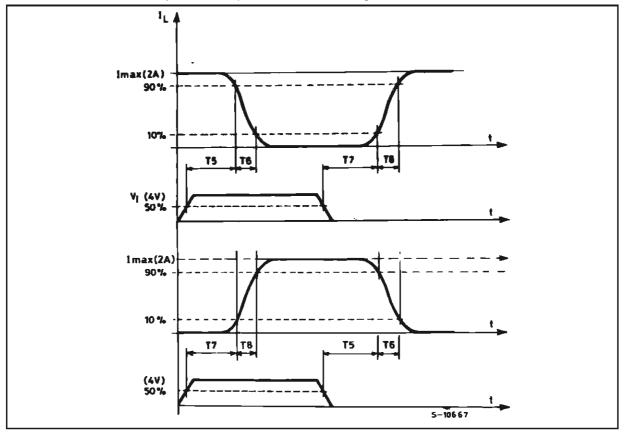
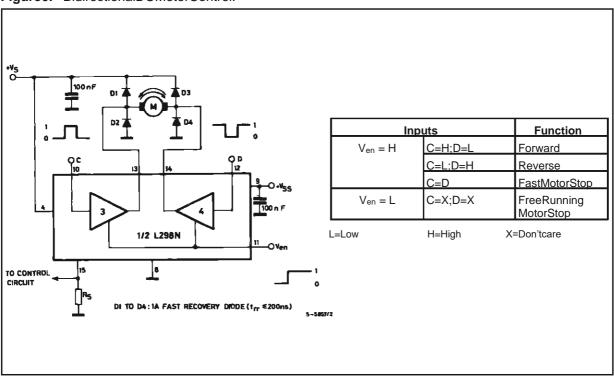
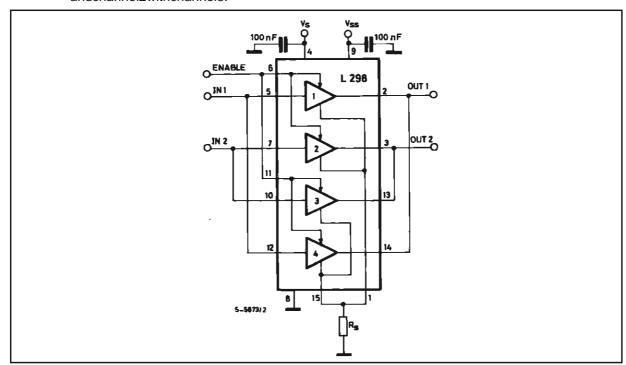


Figure6: BidirectionalDCMotorControl.





**Figure7:** Forhighercurrents,outputscanbeparalleled.Takecaretoparallelchannel1withchannel4 andchannel2withchannel3.

#### APPLICATIONINFORMATION(Refertotheblockdiagram)

#### 1.1.POWEROUTPUTSTAGE

TheL298integratestwopoweroutputstages (A;B). Thepoweroutputstageisabridgeconfiguration anditsoutputscandriveaninductiveloadincommonordifferenzialmode, depending on the state of the inputs. The current that flows through the load comes out from the bridge at the sense output: an external resistor (R sa;R sb.) allows to detect the intensity of this current.

#### 1.2.INPUTSTAGE

EachbridgeisdrivenbymeansoffourgatestheinputofwhichareIn1;In2;EnAandIn3;In4;EnB. TheIninputssetthebridgestatewhenTheEninput ishigh;alowstateoftheEninputinhibitsthebridge. AlltheinputsareTTLcompatible.

#### 2.SUGGESTIONS

Anoninductivecapacitor, usually of 100nF, must before seen between both Vs and Vss, to ground, as near aspossible to GND pin. When the large capacitor of the power supply is to of ar from the IC, a second smaller one must be for eseen near the L298.

Thesenseresistor, noto fawire wound type, must be grounded near the negative pole of Vsthat must be near the GND pin of the I.C.

Eachinputmustbeconnectedtothesourceofthe drivingsignalsbymeansofaveryshortpath.

Turn-OnandTurn-Off:BeforetoTurn-ONtheSupplyVoltageandbeforetoTurnitOFF,theEnableinputmustbedriventotheLowstate.

#### 3.APPLICATIONS

Fig6showsabidirectionalDCmotorcontrolSchematicDiagramforwhichonlyonebridgeisneeded. The external bridge of diodes D1 to D4 is made by four fast recovery elements (trr  $\leq$  200 nsec) that must be chosen of a VF as low as possible at the worst case of the load current.

Thesenseoutputvoltagecanbeusedtocontrolthe currentamplitudebychoppingtheinputs,ortoprovideovercurrentprotectionbyswitchinglowtheenableinput.

Thebrakefunction(Fastmotorstop)requiresthat the Absolute Maximum Rating of 2 Ampsmust neverbeover come.

Whentherepetitivepeakcurrentneededfromthe loadishigherthan 2 Amps, aparalleled configuration can be chosen (See Fig. 7).

Anexternalbridgeofdiodesarerequiredwheninductiveloadsaredrivenandwhentheinputsofthe ICarechopped; Shottkydiodeswouldbepreferred.

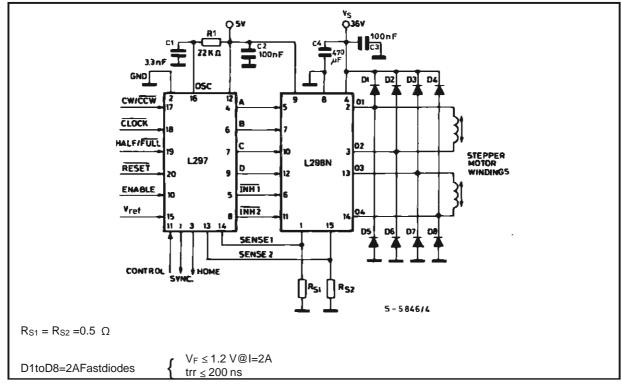
This solution can drive until 3 Amps In DC operation and until 3.5 Amps of a repetitive peak current.

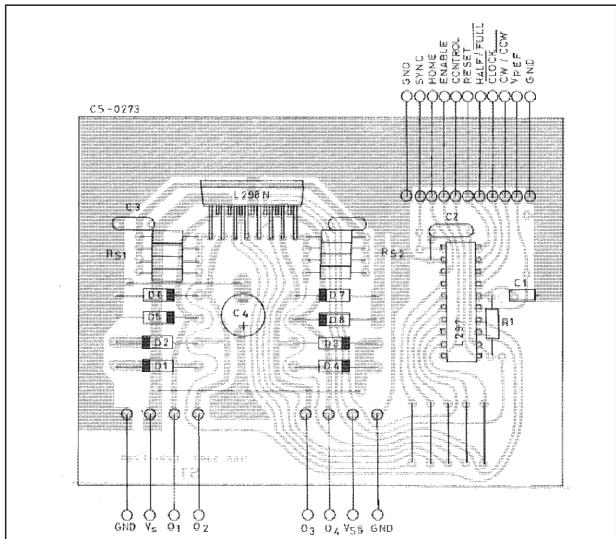
On Fig8itis shown the driving of atworphase bipolar stepper motor; the needed signal stodrive the inputs of the L298 are generated, in this example, from the ICL 297.

Figure8: TwoPhaseBipolarStepperMotorCircuit.

Fig10showsasecondtwophasebipolarstepper motorcontrolcircuitwherethecurrentiscontrolled bythel.C.L6506.

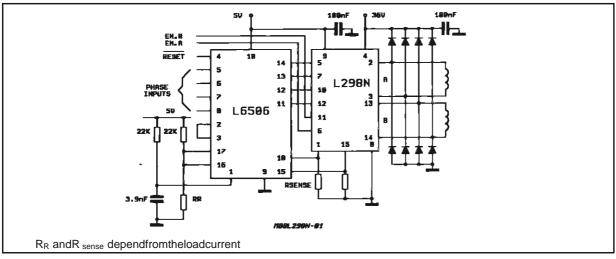
This circuit drives bipolar stepper motors with winding current sup to 2A. The diodes are fast 2A types.





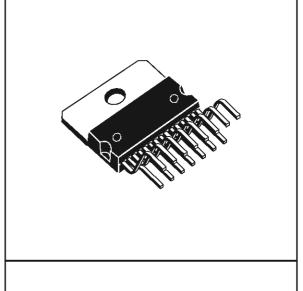
 $\textbf{Figure 9:} \quad \textbf{Suggested Printed Circuit Board Layout for the Circuit of fig. 8 (1:1 scale)}.$ 

Figure 10: Two Phase Bipolar Stepper Motor Control Circuit by Using the Current Controller L6506.

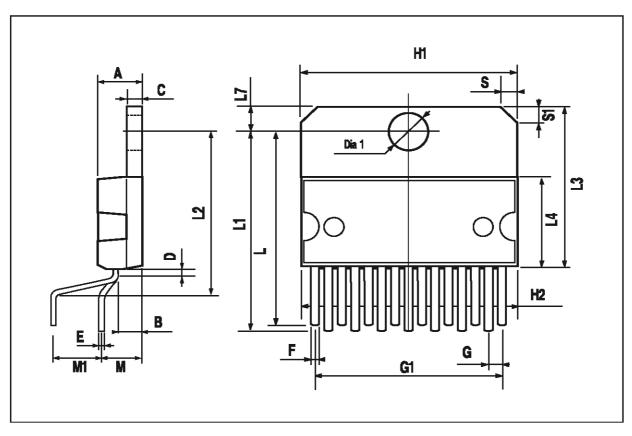


DIM		mm			inch	
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			5			0.197
В			2.65			0.104
С			1.6			0.063
D		1			0.039	
E	0.49		0.55	0.019		0.022
F	0.66		0.75	0.026		0.030
G	1.02	1.27	1.52	0.040	0.050	0.060
G1	17.53	17.78	18.03	0.690	0.700	0.710
H1	19.6			0.772		
H2			20.2			0.795
L	21.9	22.2	22.5	0.862	0.874	0.886
L1	21.7	22.1	22.5	0.854	0.870	0.886
L2	17.65		18.1	0.695		0.713
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L7	2.65		2.9	0.104		0.114
М	4.25	4.55	4.85	0.167	0.179	0.191
M1	4.63	5.08	5.53	0.182	0.200	0.218
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152

### OUTLINEAND MECHANICALDATA

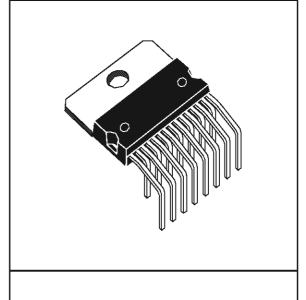


Multiwatt15V

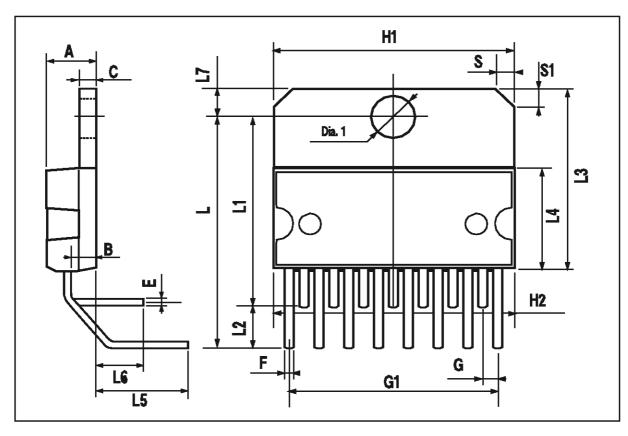


DIM.	mm			inch		
DIN.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			5			0.197
В			2.65			0.104
С			1.6			0.063
Е	0.49		0.55	0.019		0.022
F	0.66		0.75	0.026		0.030
G	1.14	1.27	1.4	0.045	0.050	0.055
G1	17.57	17.78	17.91	0.692	0.700	0.705
H1	19.6			0.772		
H2			20.2			0.795
L		20.57			0.810	
L1		18.03			0.710	
L2		2.54			0.100	
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L5		5.28			0.208	
L6		2.38			0.094	
L7	2.65		2.9	0.104		0.114
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152

### OUTLINEAND MECHANICALDATA



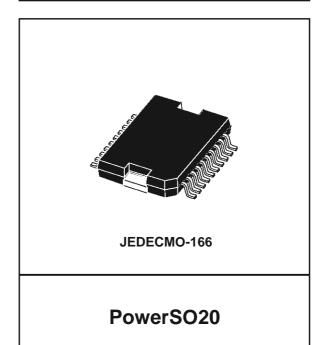
Multiwatt15H

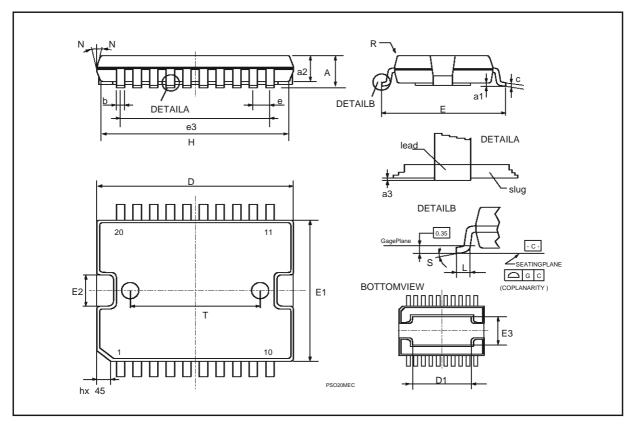


DIM		mm			inch		
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			3.6			0.142	
a1	0.1		0.3	0.004		0.012	
a2			3.3			0.130	
a3	0		0.1	0.000		0.004	
b	0.4		0.53	0.016		0.021	
С	0.23		0.32	0.009		0.013	
D(1)	15.8		16	0.622		0.630	
D1	9.4		9.8	0.370		0.386	
E	13.9		14.5	0.547		0.570	
е		1.27			0.050		
e3		11.43			0.450		
E1(1)	10.9		11.1	0.429		0.437	
E2			2.9			0.114	
E3	5.8		6.2	0.228		0.244	
G	0		0.1	0.000		0.004	
Н	15.5		15.9	0.610		0.626	
h			1.1			0.043	
L	0.8		1.1	0.031		0.043	
N	10° (max.)						
S			8° (r	nax.)			
Т		10			0.394		

- (1) "DandF"donotincludemoldflashorprotrusions.
   Moldflashorprotrusionsshallnotexceed0.15mm(0.006"
   Criticaldimensions:"E","G"and"a3"

### **OUTLINEAND MECHANICALDATA**





	L298

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